



Institute of Electrical Engineering SAS

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SC characterization at IEE Bratislava

IEE OVERVIEW

Sample Batches investigated/received:

prepared at Uni Siegen:

• **NbTiN** films on **Si** substrate — *23.11.2023 series* (30) measured Bag1 (6), rest in progress

prepared at STFC Daresbury:

- Nb₃Sn films on Cu and Sapphire substrates 1.12.2023 series (6) measured
- Nb₃Sn , Nb films on Cu substrate 12.1.2024 series (7) measured Nb3Sn (3), rest in progress
- Nb , (Nb₃Sn , NbTiN) films on Cu substrate 23.2.2024 series (7)
 waiting

prepared at INFN Legnaro:

• Nb₃Sn films on Cu, Cu+Nb and Sapphire substrates — 8.2.2024 series (6+3) measured Run#33 (3), rest in progress

Currently going into a Shutdown for maintenance, repairs, in hope for resolving the Temperature stability and cooling issues.

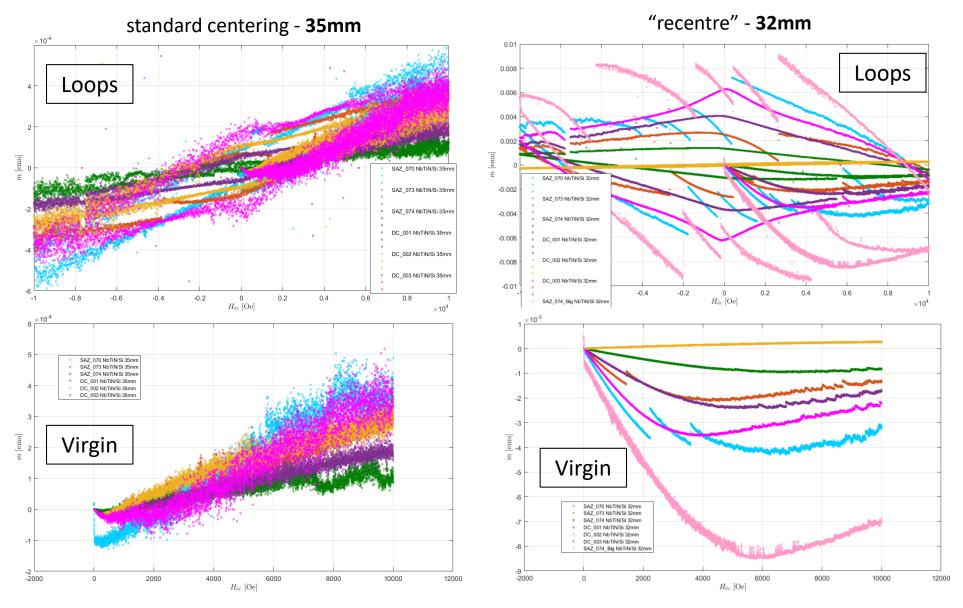
Table-summary

	Sample	Ben [Oe]	Ben [Oe]					
		(2% crit. at 4.22 K)		[K]		Ben [Oe]]	
		Perpend	Parallel		Sample	perp.	Parallel	Tc [K]
NbTiN	DC_001_recentre		870	13.8	DC_001		160	13.7
Substrate: Si	DC_002_recentre		paramag.	14.1	DC_002		130	14.2
	DC_003_recentre		670	13.7	DC_003		150	13.8
UNI Siegen	SAZ_070_recentre		25	13.5	SAZ_070		20	13.2
23.11.2023 series	SAZ_073_recentre		570	10.3	SAZ 073		150	12.7
	SAZ_074_recentre		600	12	SAZ_074		110	13.6
	(SAZ_074 B-sample_recentre)		25	14.5				
Nb3Sn	Cu_28_06_23		160	17				
Substrates: Cu, Sapphire	Cu_06_07_23		530	16.5	Cu_06_07_23_recentre		420	16.5
	Cu_24_07_23		350	17	Cu_24_07_23_recentre		190	16.1
STFC	Cu_08_12_23		300	16.7	Cu_08_12_23_recentre		700	16
1.12.2023 series	Sapp_28_06_23		50	17.5	Sapp 28 06 23 recentre		60	17.6
	Sapp_06_07_23		60	17.5	Sapp_06_07_23_recentre		60	17.4
Reza	Cu_RTdep_510C		430	14.7	Cu_RTdep_510C_recentre		100	14.7
	Sapp_24_07_23		930	17.5	Sapp_24_07_23_recentre		1080	17.6
	Cu_RTdep_340C		959		Cu_RTdep_340C		-	-
Nb3Sn	Cu_CD3MM-020		610	16.8	Cu_CD3MM-020_recentre		610	16.8
Substrate: Cu	Cu_CD3MM-002		740	16.8	Cu_CD3MM-020_recentre		700	16.8
12.1.2024 series	Cu_CD3MM-015		580	16	Cu_CD3MM-015_recentre		550	16
STFC								
D.Seal								
Nb3Sn	Cu_Run33		300	13.2	Cu_Run33_recentre		290	13.2
Substrate: Cu, Sapphire	Cu_Run33_50Nb		700	9.3 + 16.8	Cu_Run33_50Nb_recentre		720	16.8
8.2.2024 series	Sapp_Run33		860	16.8	Sapp_Run33_recentre		900	16.8
INFN					10.0000 a 4.00			
Dorothea Fonnesu								

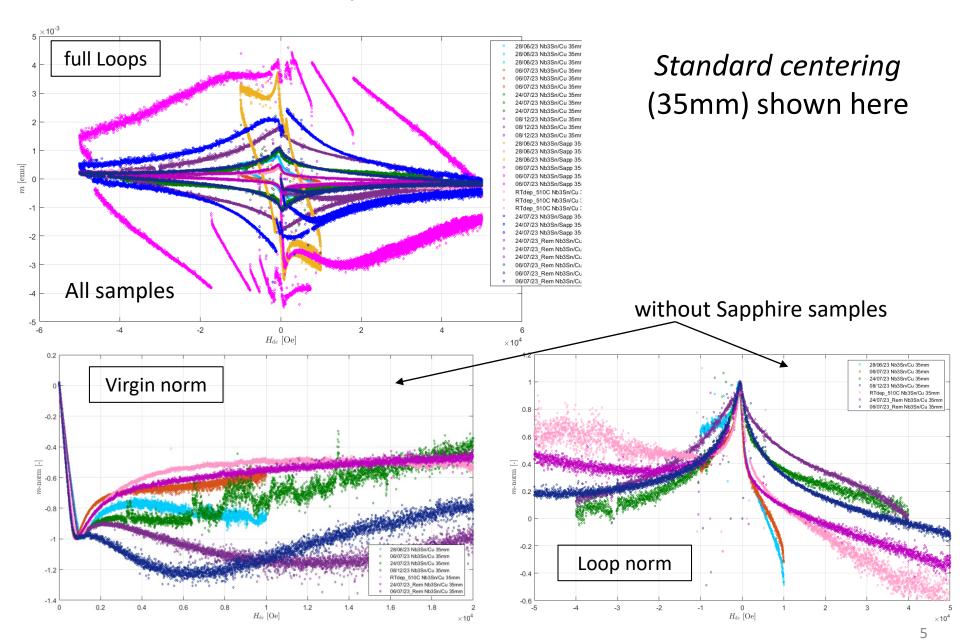
[&]quot;Mystery issues" regarding sample centering in the VSM coil pair

Majority of samples measured in a standard and in a shifted position ('_recentre')

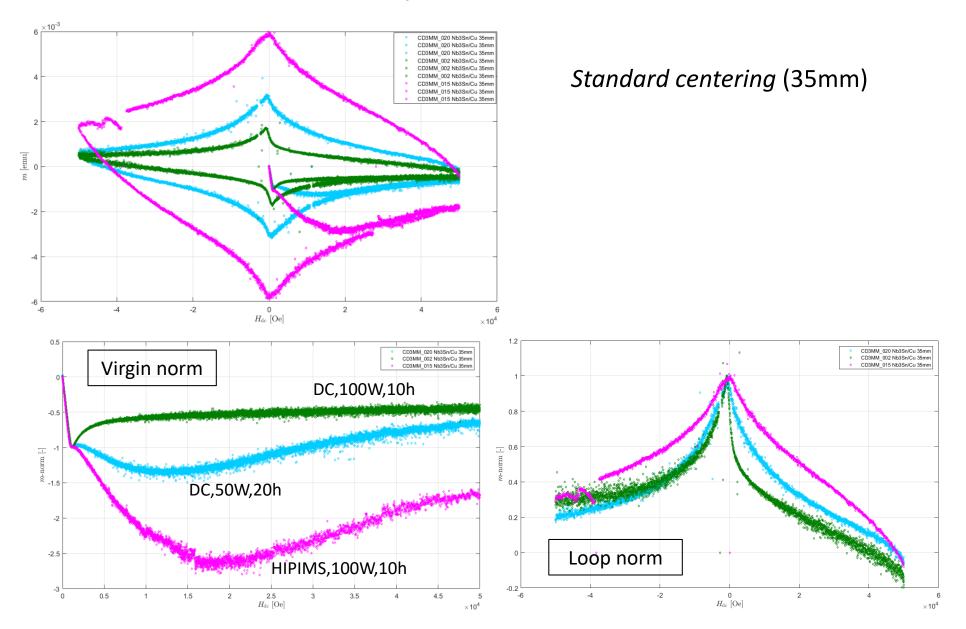
NbTiN / Si UniSiegen (23.11.2023 series, Bag1)



Nb₃Sn / Cu,Sapp STFC (1.12.2023 series)

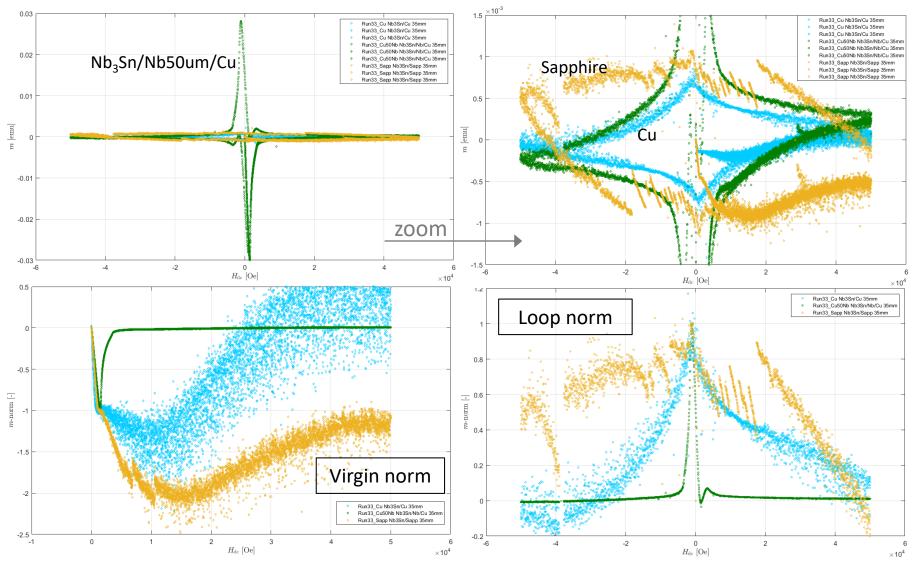


Nb₃Sn / Cu STFC (from 12.1.2024 series)



Nb₃Sn / Cu,Cu+Nb,Sapp INFN (Run 33, 8.2.2024 series)

Standard centering (35mm)



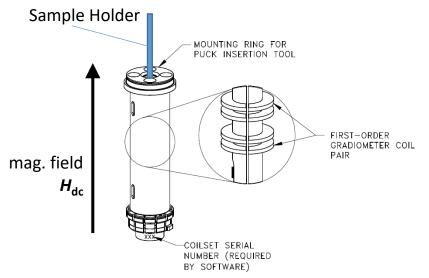
Run 33: deposition 600°C, Nb₃Sn-1μm

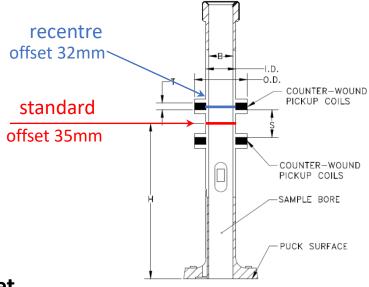
Sapphire sample – 'Smash-cleaving'

Thank you for your attention

Appendix: Sample centering issues

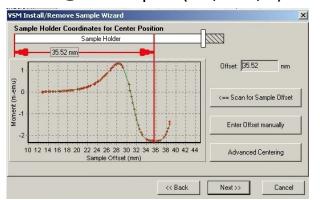
Brief introduction



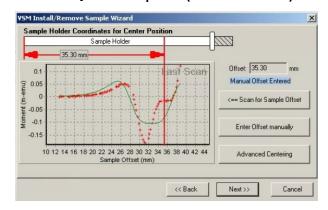


Moment vs. Sample Offset

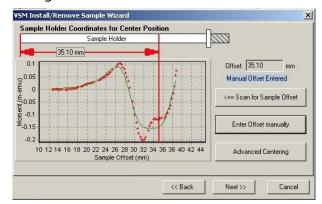
Usual @SC samples (Nb, HTS,...)



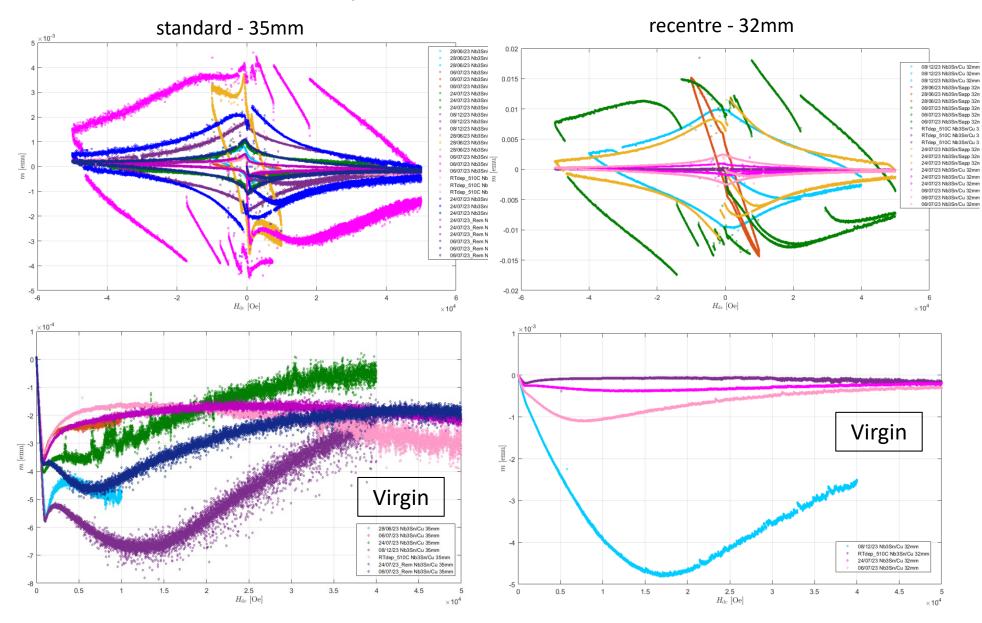
NbTiN/Si samples (23.11.2023)

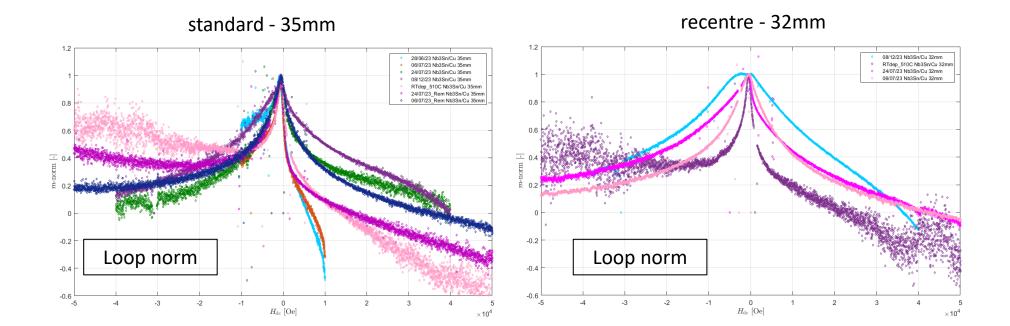


Nb₃Sn samples

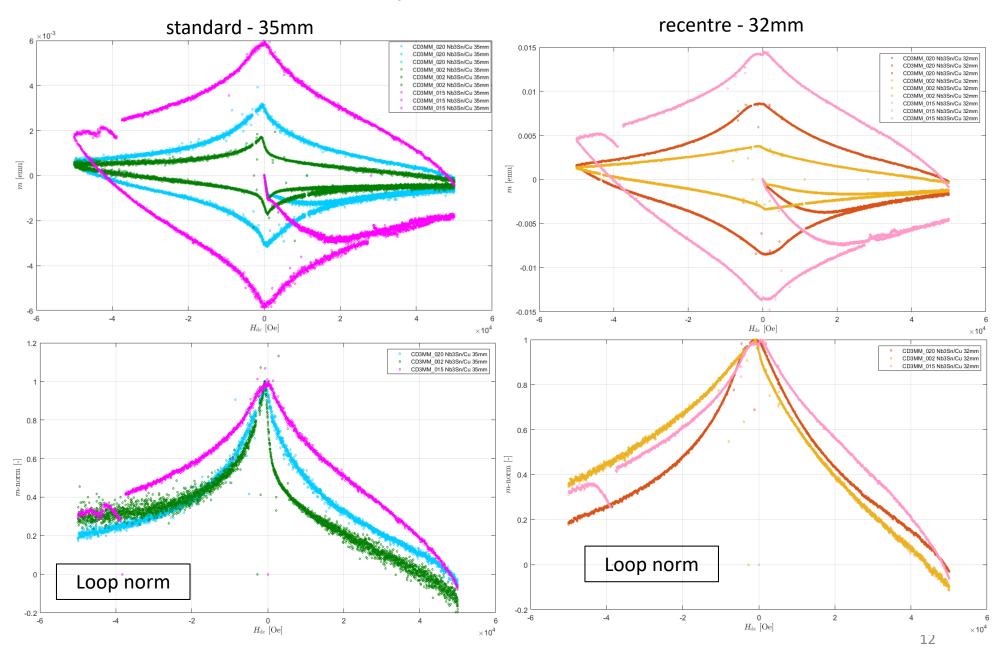


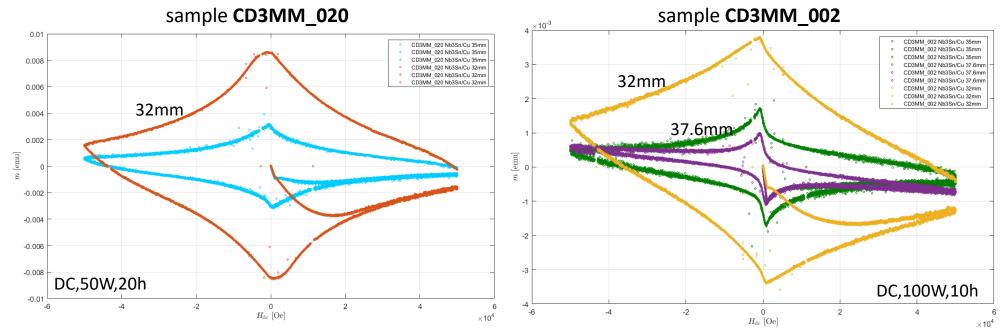
Nb₃Sn / Cu,Sapp STFC (1.12.2023 series)

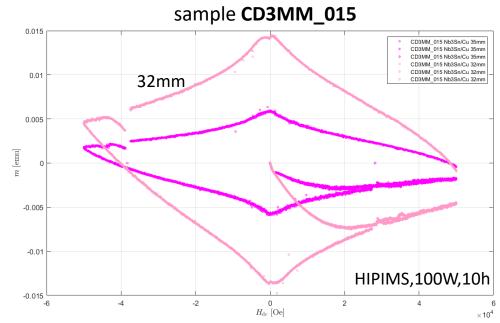




Nb₃Sn / Cu STFC (from 12.1.2024 series)







Nb₃Sn / Cu,Cu+Nb,Sapp INFN (Run 33, 8.2.2024 series)

